

# FQP32N20C/FQPF32N20C

## 200V N-Channel MOSFET

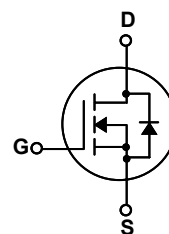
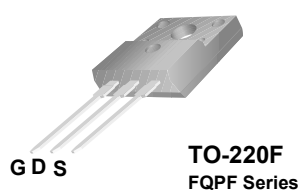
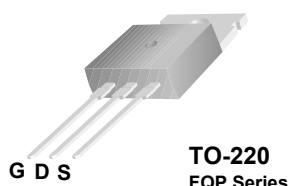
### General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supplies, DC-AC converters for uninterrupted power supplies and motor controls.

### Features

- 28A, 200V,  $R_{DS(on)} = 0.082\Omega @ V_{GS} = 10V$
- Low gate charge ( typical 82.5 nC)
- Low  $C_{rss}$  ( typical 185 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQP32N20C	FQPF32N20C	Units
$V_{DSS}$	Drain-Source Voltage	200		V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) - Continuous ( $T_C = 100^\circ\text{C}$ )	28.0	28.0 *	A
		17.8	17.8 *	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	112	112 *	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$		V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	955		mJ
$I_{AR}$	Avalanche Current (Note 1)	28.0		A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	15.6		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5		V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ ) - Derate above $25^\circ\text{C}$	156	50	W
		1.25	0.4	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		$^\circ\text{C}$

\* Drain current limited by maximum junction temperature.

### Thermal Characteristics

Symbol	Parameter	FQP32N20C	FQPF32N20C	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.8	2.51	$^\circ\text{C}/\text{W}$
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	$^\circ\text{C}/\text{W}$

## Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	200	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.24	--	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	$\mu\text{A}$
		$V_{DS} = 160\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 14\text{ A}$	--	0.068	0.082	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 14\text{ A}$ (Note 4)	--	20	--	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1700	2220	pF
$C_{oss}$	Output Capacitance		--	400	520	pF
$C_{riss}$	Reverse Transfer Capacitance		--	185	245	pF

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100\text{ V}, I_D = 32\text{ A},$ $R_G = 25\ \Omega$	--	25	60	ns
$t_r$	Turn-On Rise Time		--	270	550	ns
$t_{d(off)}$	Turn-Off Delay Time		--	245	500	ns
$t_f$	Turn-Off Fall Time		(Note 4, 5)	--	210	430
$Q_g$	Total Gate Charge	$V_{DS} = 160\text{ V}, I_D = 32\text{ A},$ $V_{GS} = 10\text{ V}$	--	82.5	110	nC
$Q_{gs}$	Gate-Source Charge		--	10.5	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4, 5)	--	44.5	--

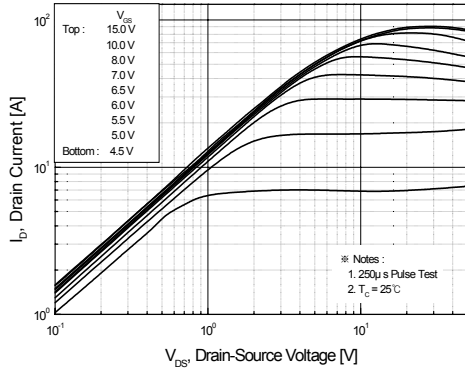
### Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	28	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	112	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 28\text{ A}$	--	--	1.5	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 32\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	265	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	2.73	--	$\mu\text{C}$

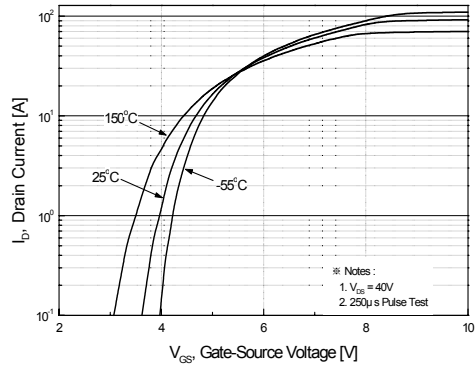
#### Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 1.4\text{ mH}, I_{AS} = 32\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 28\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\ \mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

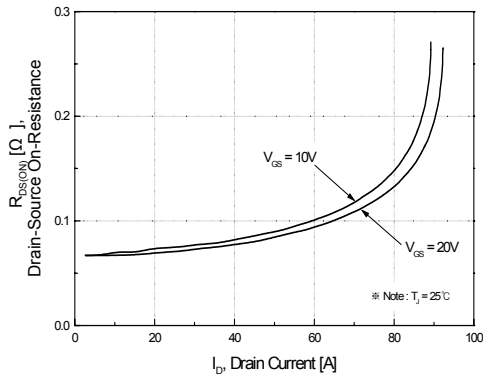
## Typical Characteristics



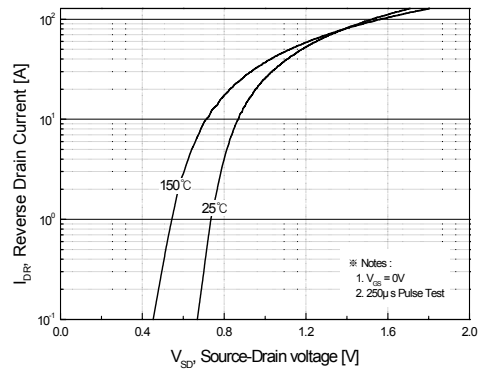
**Figure 1. On-Region Characteristics**



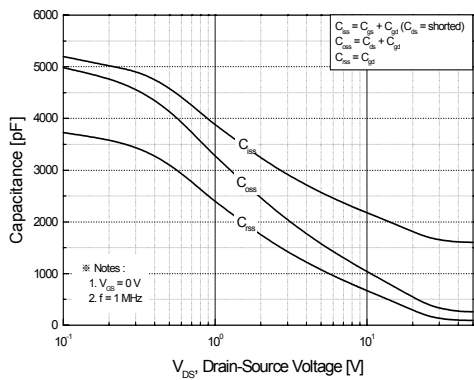
**Figure 2. Transfer Characteristics**



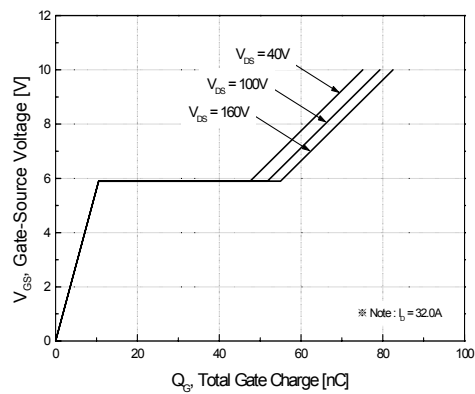
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



**Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature**

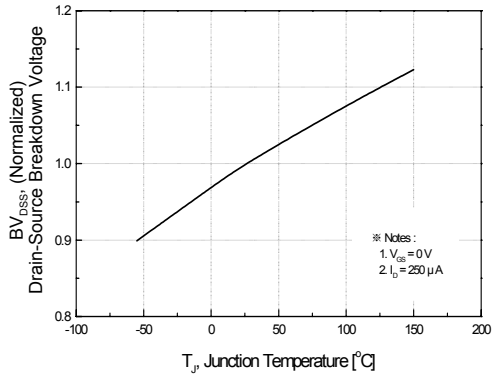


**Figure 5. Capacitance Characteristics**

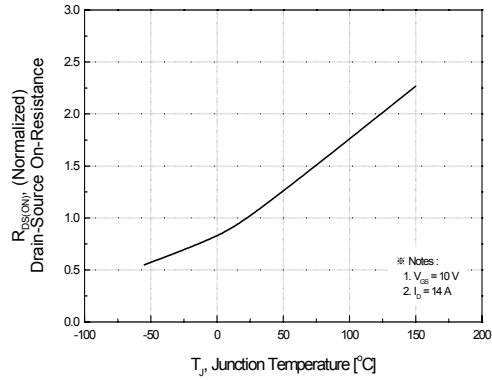


**Figure 6. Gate Charge Characteristics**

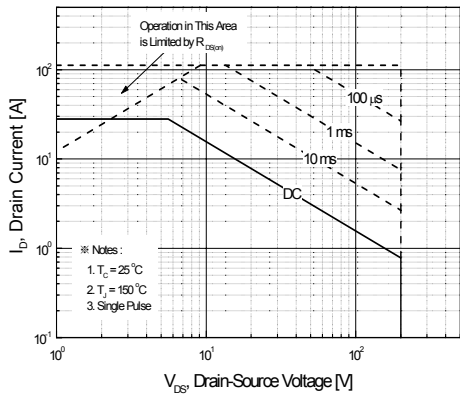
**Typical Characteristics** (Continued)



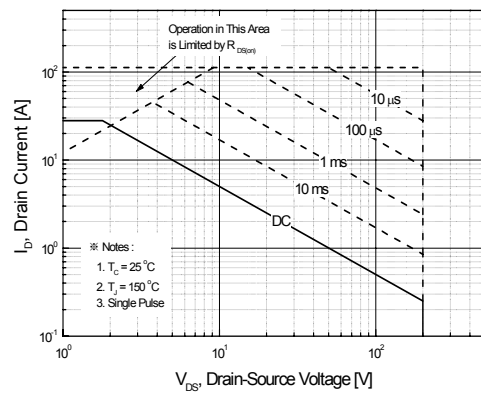
**Figure 7. Breakdown Voltage Variation vs Temperature**



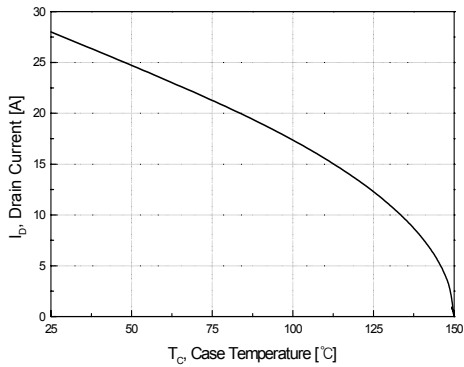
**Figure 8. On-Resistance Variation vs Temperature**



**Figure 9-1. Maximum Safe Operating Area for FQP32N20C**



**Figure 9-2. Maximum Safe Operating Area for FQPF32N20C**



**Figure 10. Maximum Drain Current vs Case Temperature**

Typical Characteristics (Continued)

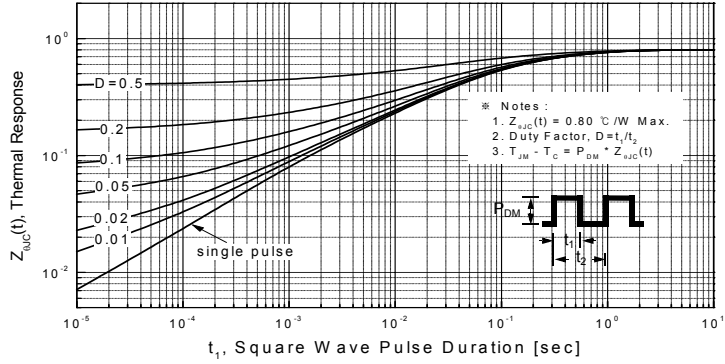


Figure 11-1. Transient Thermal Response Curve for FQP32N20C

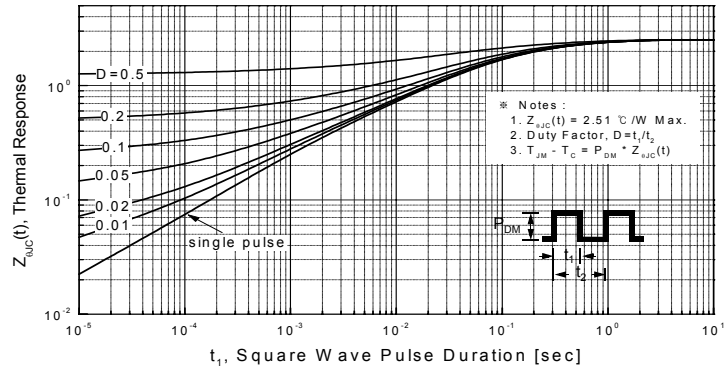
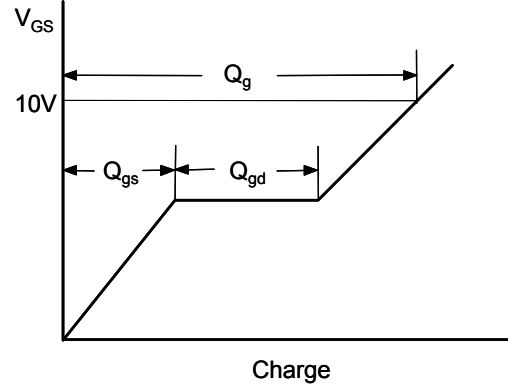
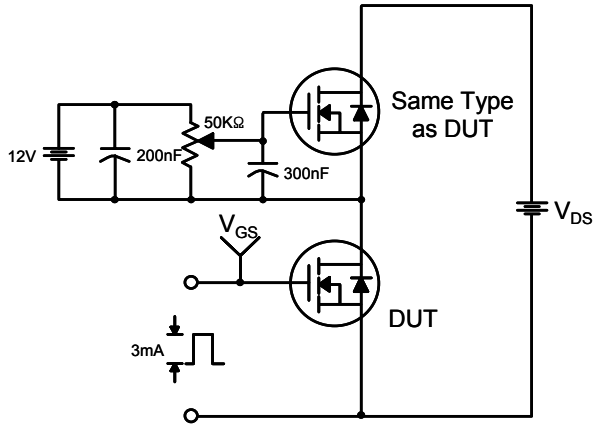
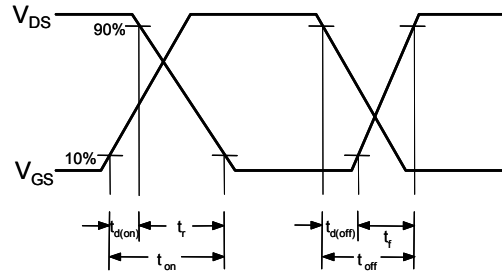
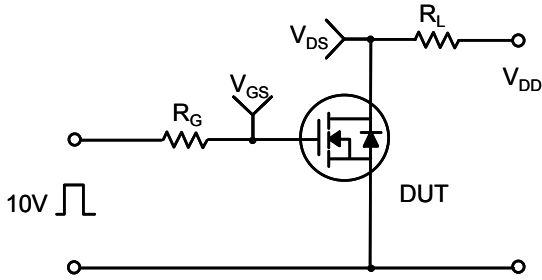


Figure 11-2. Transient Thermal Response Curve for FQPF32N20C

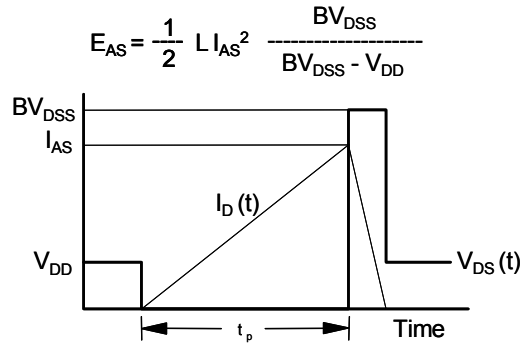
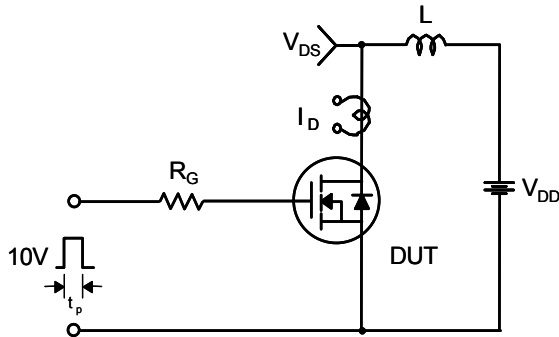
**Gate Charge Test Circuit & Waveform**



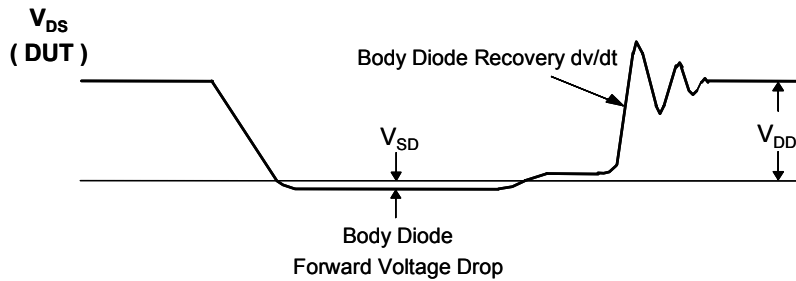
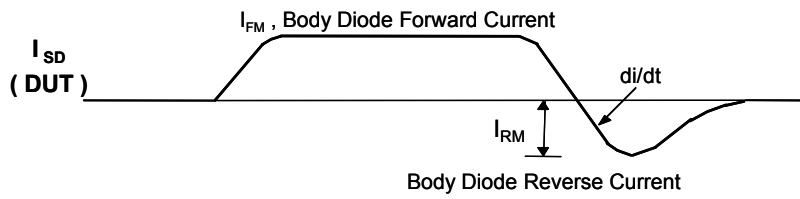
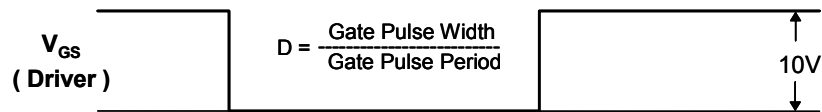
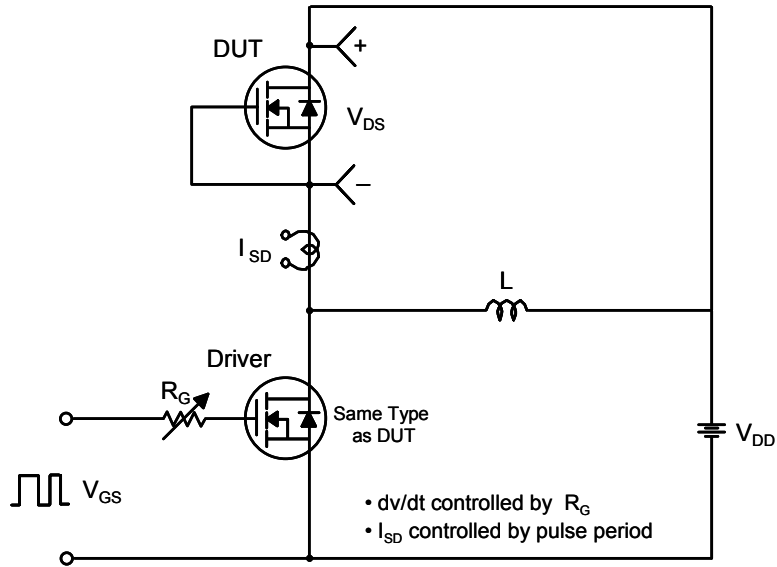
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

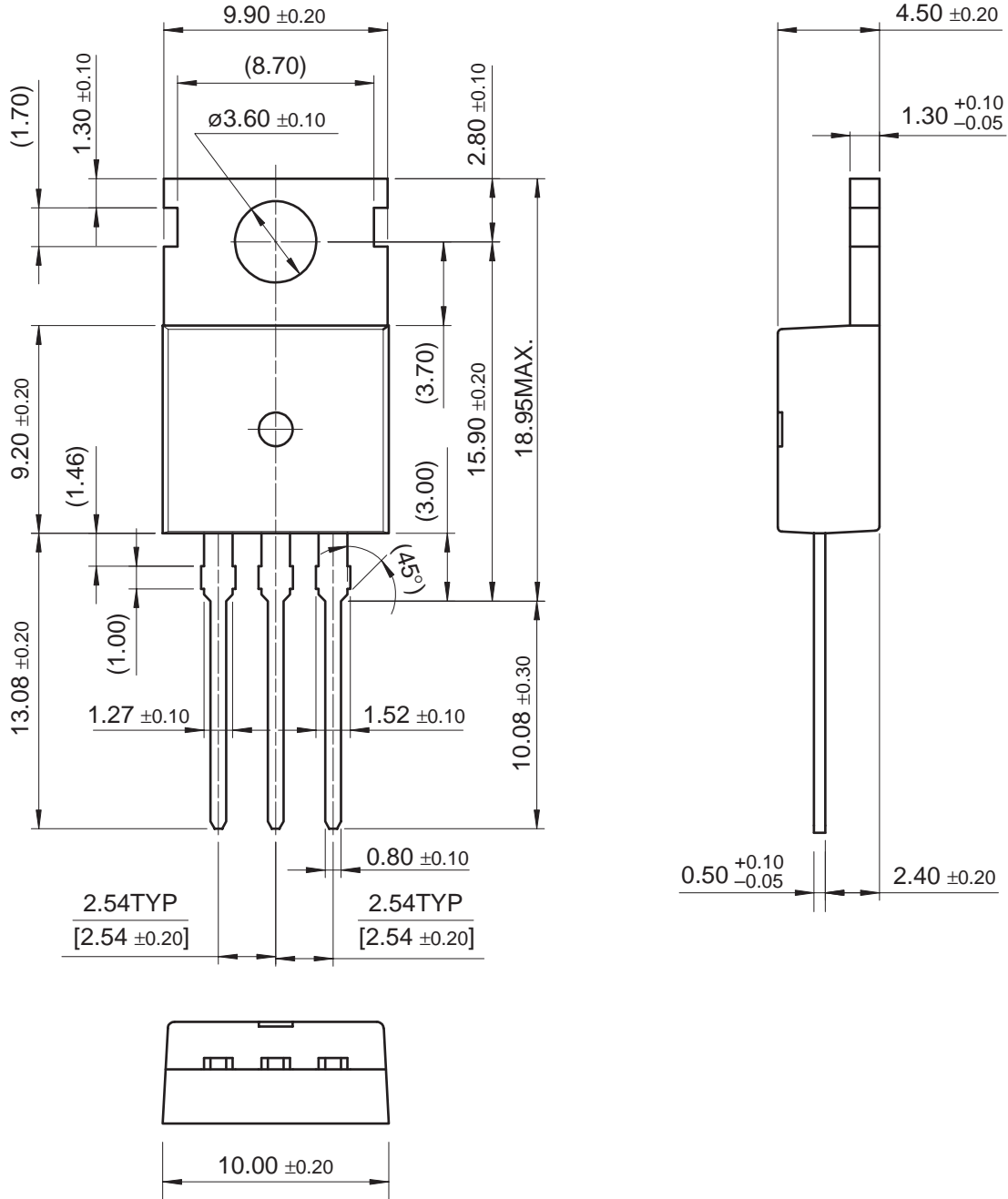


Peak Diode Recovery dv/dt Test Circuit & Waveforms



# Package Dimensions

## TO-220

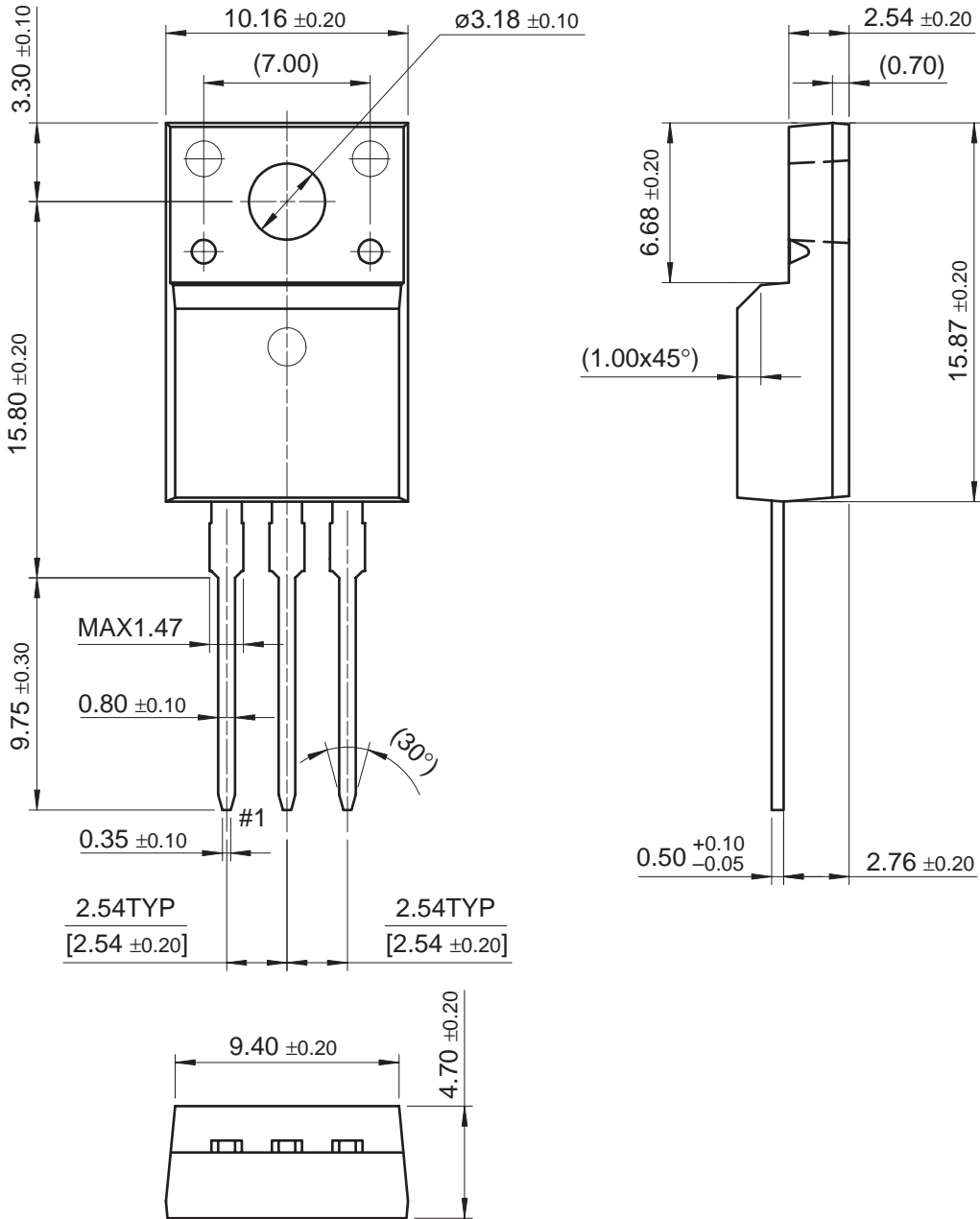


FQP32N20C/FQPF32N20C

Dimensions in Millimeters

Package Dimensions (Continued)

TO-220F



FQP32N20C/FQPF32N20C

Dimensions in Millimeters

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